Supporting Information

Nitrogen and Sulfur Co-Doped $Ti_3C_2T_x$ MXene for High-Rate Lithium-Ion Batteries

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Fig. S1 SEM images of (a) $Ti_3C_2T_x$, (b) $N-Ti_3C_2T_x$, (c) $NS_{0.1}-Ti_3C_2T_x$, and (d) $NS_{0.5}-Ti_3C_2T_x$.



Fig. S2 (a) $NS_{0.1}$ -Ti₃C₂ T_x , corresponding elemental mapping images (b) for the distribution of Ti, N, O and S elements, respectively. (c) $NS_{0.5}$ -Ti₃C₂ T_x , corresponding elemental mapping images (d) for the distribution of Ti, C, O and S elements, respectively.



Fig. S3 Typical STEM image and EDS mapping of $NS_{0.3}$ -Ti₃C₂ T_x . (a) Cross sectional microstructure of $NS_{0.3}$ -Ti₃C₂ T_x . (b) HAADF image of marked area by green rectangular and (c) corresponding elemental mappings of Ti, C, N, and S elements. (d) STEM-EDS spectrum of $NS_{0.3}$ -Ti₃C₂ T_x . The atomic ratios of elements are listed in Table S1.



Fig. S4 Nitrogen adsorption/desorption isotherms of (a) pristine $Ti_3C_2T_x$, (b) $NS_{0.1}-Ti_3C_2T_x$, (c) $NS_{0.3}-Ti_3C_2T_x$ and (d) $NS_{0.5}-Ti_3C_2T_x$. The BET specific surface areas of aforementioned samples are 3.2, 6.4, 2.0 and 1.9 m² g⁻¹, respectively.



Fig. S5 (a) XRD patterns and (b) Raman spectra of pristine $Ti_3C_2T_x$ and N, S codoped $Ti_3C_2T_x$.



Fig. S6 (a) XPS survey spectra of pristine $Ti_3C_2T_x$, $N-Ti_3C_2T_x$, $NS_{0.1}-Ti_3C_2T_x$, $NS_{0.3}-Ti_3C_2T_x$, and $NS_{0.5}-Ti_3C_2T_x$. High-resolution C 1s XPS spectra of (b) $Ti_3C_2T_x$, (c) $N-Ti_3C_2T_x$, (d) $NS_{0.1}-Ti_3C_2T_x$, (e) $NS_{0.3}-Ti_3C_2T_x$, and (f) $NS_{0.5}-Ti_3C_2T_x$. The XPS spectra were recorded after Ar sputtering for 120 s.



Fig. S7 High-resolution Ti 2p XPS spectra of pristine $Ti_3C_2T_x$. The XPS spectra were recorded after Ar sputtering for 120 s.



Fig. S8 CV curves of (a) pristine $Ti_3C_2T_x$, (c) $NS_{0.1}$ - $Ti_3C_2T_x$, (e) $NS_{0.5}$ - $Ti_3C_2T_x$ electrodes. Galvanostatic charge and discharge curves of (b) N- $Ti_3C_2T_x$, (d) $NS_{0.1}$ - $Ti_3C_2T_x$ and (f) $NS_{0.5}$ - $Ti_3C_2T_x$ cycled at various rates.



Fig. S9 Diffusion barrier profiles of Li on (a) $Ti_3C_2O_2$, (b) $Ti_3C_2N_2$, (c) $Ti_3C_2S_2$ and (d) $Ti_3C_2(NS)_2$ and the corresponding energetically optimized Li migration pathways from side and top view.



Fig. S10 XRD pattern of the as-prepared $LiMn_{0.5}Fe_{0.5}PO_4$ product. TEM image (b), and SEM images (c, d) of $LiMn_{0.5}Fe_{0.5}PO_4/C$ material.



Fig. S11 (a) Typical charge/discharge curves of $LiMn_{0.5}Fe_{0.5}PO_4/C$ at current rates ranging from 0.1 to 10C. (b) Rate capability.

Table S1 Summary of atomic ratio in the $NS_{0.3}$ -Ti₃C₂ T_x .

NS _{0.3} -Ti ₃ C ₂ T	Element							
x	С	0	F	Al	Si	S	Ti	Cu
Subsurface	25.22	13.59	5.02	0.68	0.35	1.11	45.36	8.67
Interior	20.58	11.99	5.16	0.56	0.42	0.70	51.27	9.31

Table S2 Atomic concentration of elements in surface layers of pristine– $Ti_3C_2T_x$, N– $Ti_3C_2T_x$, NS_{0.1}– $Ti_3C_2T_x$, NS_{0.3}– $Ti_3C_2T_x$, and NS_{0.5}– $Ti_3C_2T_x$, samples.

Samula				Element			
Sample	Ti	0	С	F	Al	Ν	S
pristine–Ti ₃ C ₂ T_x	19.0	21.3	36.0	14.4	9.3	-	-
N–Ti ₃ C ₂ T_x	27.2	25.1	32.1	7.4	5.2	3.0	-
$NS_{0.1}-Ti_3C_2T_x$	10.9	17.4	52.6	8.2	6.9	2.5	1.5
$NS_{0.3}-Ti_3C_2T_x$	12.0	16.7	55.3	7.8	3.4	2.0	2.9
$NS_{0.5}$ - $Ti_3C_2T_x$	11.1	15.3	54.2	9.6	3.5	3.5	2.8

Table S3 Ti 2p core level peak analyses of $Ti_3C_2T_x$ MXenes after Ar⁺ sputtering 120 s. The Ti 2p core level was fitted with a fixed area ratio of 2:1 for all Ti $2p_{3/2}$ -Ti $2p_{1/2}$ and doublet separation of 5.5 eV for C–Ti–C, C–Ti–OH, C–Ti–O, C–Ti–S, C–Ti–N, and C–Ti–ON.

	Fraction / %					
Sample	C–Ti–C	C-Ti-N	C-Ti-OH	C–Ti–S	C-Ti-O	C-Ti-ON
	454.9±0.1eV	455.5±0.1eV	456.3±0.1eV	457.0±0.1eV	457.2eV±0.1eV	458.2±0.1eV
pristine-Ti ₃ C ₂ T		_	28.6			—
x	53.6			_	17.8	
N–Ti ₃ C ₂ T_x	40	5.0	_	_	50	5.0
$NS_{0.1}-Ti_3C_2T_x$	42.3	6.3	_	4.2	40.9	6.3
$NS_{0.3}$ - $Ti_3C_2T_x$	41.5	1.2	_	5.0	49.8	2.5
$NS_{0.5}$ - $Ti_3C_2T_x$	45.2	3.1	-	6.2	42.4	3.1

Samples	Volume expansion (%)	Reference
$NS_{0.3}$ -Ti ₃ C ₂ T_x	0.6	This work
LiCoO ₂	1.8	Ref. ¹
VPO ₄	2.1	Ref. ²
NCM111	1.2	Ref. ³
Nb_2CT_x	2.3	Ref. ⁴
LiFePO ₄	6.8	Ref. ⁵
VO ₂	6.0	Ref. ⁶
LiMn ₂ O ₄	16	Ref. ⁷
Li ₄ Ti ₅ O ₁₂	0.8	Ref. ⁸
Graphite	10.7	Ref. ⁹
TiO ₂	3.7	Ref. ¹⁰

Table S4. Comparison of the volume expansion for $NS_{0.3}$ -Ti₃C₂ T_x in our work with widely reported electrode materials.

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